

## NTH4L018N075SC1

### Silicon Carbide (SiC) MOSFET, N-Channel - EliteSiC, 13.5mohm, 750V, M2, TO247-4L

## Product Overview

For complete documentation, see the data sheet.

EliteSiC MOSFET uses a completely new technology that provide superior switching performance and higher reliability compared to Silicon. In addition, the low ON resistance and compact chip size ensure low capacitance and gate charge. Consequently, system benefits include highest efficiency, faster operation frequency, increased power density, reduced EMI, and reduced system size.

## Features

- $T_J = 175^\circ\text{C}$
- Ultra Low Gate Charge (Typ.  $Q_g = 262 \text{ nC}$ )
- High Speed Switching with Low Capacitance ( $C_{oss} = 365 \text{ pF}$ )
- Zero reverse recovery current of body diode
- Kelvin Source configuration
- Typ.  $R_{DS(on)} = 13.5 \text{ m at } V_{gs} = 18\text{V}$
- 100% UIL Tested
- RoHS Compliant

## Applications

- Industrial

## End Products

- UPS / ESS
- Solar
- EV Charger

## Part Electrical Specifications

Product	Status	Compliance	Family	Blocking Voltage $\text{BV}_{DS}$ (V)	$I_{D(\text{max})}$ (A)	$R_{DS(on)}$ Typ @ $25^\circ\text{C}$ (mΩ)	$Q_g$ Total (nC)	Output Capacitance (pF)	$T_J$ Max ( $^\circ\text{C}$ )	Package Type	Case Outline	MSL Type	MSL Temp ( $^\circ\text{C}$ )	Container Type	Container Qty.
NTH4L018N075SC1	Active		M2	750	140	13.5	262	365	175	TO-247-4	340 C.J.P DF	1	245	TUBE	450